

A5G26H606W19N

Airfast RF Power GaN Amplifier

Rev. 3.0 — 13 February 2026

Product data sheet



1 General description

This 85 W asymmetrical Doherty RF power GaN amplifier is designed for cellular base station applications requiring very wide instantaneous bandwidth capability covering the frequency range of 2496 to 2690 MHz.

This part is characterized and performance is guaranteed for applications operating in the 2496 to 2690 MHz band. There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

2 Features and benefits

- High terminal impedances for optimal broadband performance
- Advanced high performance in-package Doherty
- Improved linearized error vector magnitude with next generation signal
- Able to withstand extremely high output VSWR and broadband operating conditions
- Plastic package

3 Typical performance

Table 1. 2600 MHz — Typical Doherty single-carrier W-CDMA reference circuit performance

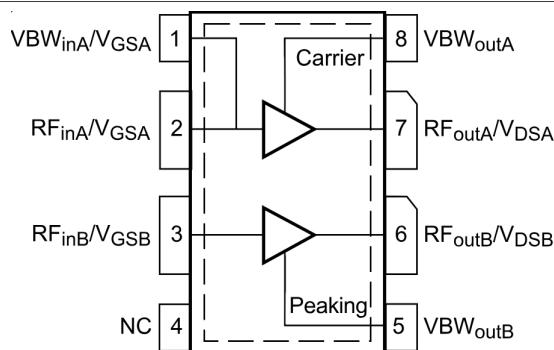
$V_{DD} = 48 \text{ Vdc}$, $I_{DQA} = 300 \text{ mA}$, $V_{GSB} = -4.5 \text{ Vdc}$, $P_{out} = 85 \text{ W Avg.}$, input signal PAR = 9.9 dB @ 0.01 % probability on CCDF.^[1]

Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)
2496 MHz	14.3	53.6	7.9	-27.8
2595 MHz	14.6	52.3	7.9	-32.7
2690 MHz	13.9	50.8	8.0	-35.4

[1] All data measured with device soldered to NXP reference circuit.



4 Pinning information



Note: Exposed backside of the package is the source terminal for the amplifier.

Figure 1. Pin configuration

5 Ordering information

Table 2. Ordering information

Device	Tape and reel information	Package
A5G26H606W19NR3	R3 suffix = 250 units, 44 mm tape width, 13-inch reel	OM-780-4S4S

6 Product marking



Figure 2. Product marking

Table 3. Product marking trace code

Identifier	Description
AA	Assembly location
WL	Wafer lot indicator
YYWW	Date code
ZZ	Assembly lot

7 Limiting values

Table 4. Limiting values

Symbol	Parameter	Conditions	Value	Unit
V_{DSS}	Drain-source voltage		125	Vdc
V_{GS}	Gate-source voltage		-8, 0	Vdc
V_{DD}	Operating voltage		55	Vdc
I_{GMAX}	Maximum forward gate current	$I_G (A+B)$, @ $T_C = 25^\circ\text{C}$	90	mA
T_{stg}	Storage temperature range		-65 to +150	°C
T_{CH}	Maximum channel temperature		225	°C

8 Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Value	Unit
V_{DD}	Operating voltage		48	Vdc

9 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta SC}$ (IR)	Thermal resistance by infrared measurement, active die surface-to-case	Case temperature 122 °C, $P_{D-Global} = 102$ W	0.48 ^[1]	°C/W
$R_{\theta CHC}$ (FEA)	Thermal resistance by finite element analysis, channel-to-case	Carrier (case temperature 122 °C, $P_D = 62$ W)	1.3 ^{[1][2]}	°C/W
		Peaking (case temperature 115 °C, $P_D = 22$ W)	1.0 ^{[1][2]}	°C/W

[1] Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <https://www.nxp.com/RF> and search for AN1955.

[2] $R_{\theta CHC}$ (FEA) must be used for purposes related to reliability and limitations on maximum channel temperature. MTTF may be estimated by the expression MTTF (hours) = $10^{A+B/(T+273)}$, where T is the channel temperature in degrees Celsius, A = -11.6 and B = 9129.

10 ESD protection characteristics

Table 7. ESD protection characteristics

Test methodology	Class
Human Body Model (per JS-001-2023)	1B
Charge Device Model (per JS-002-2022)	C3

11 Moisture sensitivity level

Table 8. Moisture sensitivity level

Test methodology	Rating	Package peak temperature	Unit
Per JESD22-A113, IPC/JEDEC J-STD-020	3	245	°C

12 Electrical characteristics

12.1 DC characteristics — off characteristics

Table 9. DC characteristics — off characteristics

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off characteristics^[1]						
$I_{D(BR)}$	Off-state drain leakage	Carrier ($V_{DS} = 150$ Vdc, $V_{GS} = -8$ Vdc)	-	-	13.2	mAdc
		Peaking ($V_{DS} = 150$ Vdc, $V_{GS} = -8$ Vdc)	-	-	26.4	mAdc

[1] Each side of device measured separately.

12.2 DC characteristics — on characteristics

Table 10. DC characteristics — on characteristics

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On characteristics — Side A, Carrier						
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = 10$ Vdc, $I_D = 30$ mAdc	-4.6	-2.5	-1.9	Vdc
$V_{GSA(Q)}$	Gate quiescent voltage	$V_{DD} = 48$ Vdc, $I_{DA} = 300$ mAdc ^[1]	-3.1	-2.5	-2.1	Vdc
On characteristics — Side B, Peaking						
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = 10$ Vdc, $I_D = 60$ mAdc	-4.6	-2.6	-1.9	Vdc

[1] Measured in functional test.

12.3 Functional tests

Table 11. Functional tests

(In NXP Doherty production test fixture, $T_A = 25^\circ\text{C}$ unless otherwise noted, 50 ohm system)^[1] $V_{DD} = 48$ Vdc, $I_{DQA} = 300$ mA, $V_{GSB} = (V_t - 2.07)$ Vdc, $P_{out} = 85$ W Avg., $f = 2690$ MHz, single-carrier W-CDMA, IQ magnitude clipping, input signal PAR = 9.9 dB @ 0.01 % probability on CCDF. ACPR measured in 3.84 MHz channel bandwidth @ ± 5 MHz offset.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_{ps}	Power gain		12.8	13.7	17.8	dB
η_D	Drain efficiency		47.5	51.5	-	%
P_{sat}	Saturated power	Pulsed CW, 5 % duty cycle	55.8	56.5	-	dBm
ACPR	Adjacent channel power ratio		-	-37.6	-28.0	dBc

[1] Internally matched part.

12.4 Wideband ruggedness

Table 12. Wideband ruggedness

(In NXP Doherty production test fixture, $T_A = 25^\circ\text{C}$ unless otherwise noted, 50 ohm system) $I_{DQA} = 300\text{ mA}$, $V_{GSB} = -4.5\text{ Vdc}$, $f = 2595\text{ MHz}$, Additive White Gaussian Noise (AWGN) with 10 dB PAR.

Characteristic	Test results
ISBW of 400 MHz at 55 Vdc, 138 W Avg. modulated output power (3 dB input overdrive from 85 W Avg. modulated output power)	No device degradation

12.5 Typical performance

Table 13. Typical performance

(In NXP Doherty reference circuit, $T_A = 25^\circ\text{C}$ unless otherwise noted, 50 ohm system) $V_{DD} = 48\text{ Vdc}$, $I_{DQA} = 300\text{ mA}$, $V_{GSB} = -4.5\text{ Vdc}$, 2496–2690 MHz bandwidth.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Pulsed CW, 10 % duty cycle						
P_{sat}	Saturated power ^[1]		-	624	-	W
Φ	AM/PM ^[1] (Phase deviation from rated power to saturated power. Maximum number measured across the 2496–2690 MHz bandwidth.)		-	-11	-	°
ΔG	Gain variation @ Avg. power over temperature	-40 °C to +85 °C	-	0.018	-	dB/°C
ΔP_{sat}	Output power variation @ saturated power over temperature	-40 °C to +85 °C	-	0.003	-	dB/°C
Single-carrier W-CDMA, unclipped						
G_F	Gain flatness ^[1]	194 MHz bandwidth @ $P_{\text{out}} = 85\text{ W Avg.}$	-	0.5	-	dB
2-tone CW						
VBW_{res}	VBW resonance ^{[1][2]}		-	290	-	MHz

[1] All data measured with device soldered to NXP reference circuit.

[2] IMD third order inflection point.

Correct biasing sequence for GaN depletion mode amplifiers in a Doherty configuration

Bias ON the device

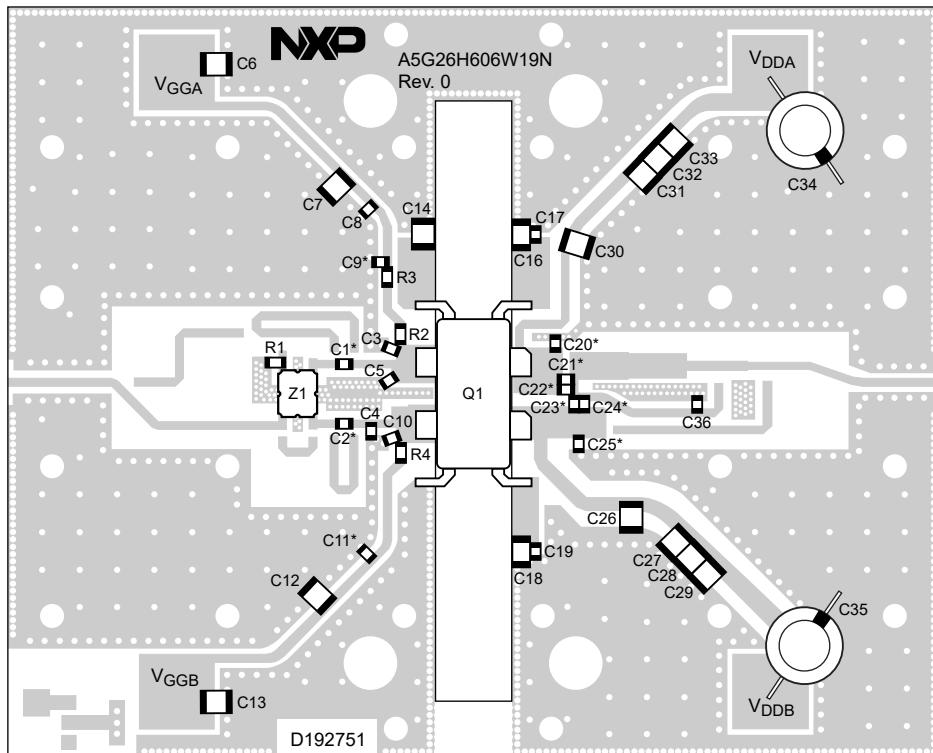
1. Set gate voltage V_{GSA} and V_{GSB} to -5 V.
2. Set drain voltage V_{DSA} and V_{DSB} to nominal supply voltage (+48 V).
3. Increase V_{GSA} (carrier side) until I_{DQA} current is attained.
4. Increase V_{GSB} (peaking side) to target bias voltage.
5. Apply RF input power to desired level.

Bias OFF the device

1. Disable RF input power.
2. Adjust gate voltage V_{GSA} and V_{GSB} to -5 V.
3. Adjust drain voltage V_{DSA} and V_{DSB} to 0 V. Allow adequate time for drain voltage to reduce to 0 V from external drain capacitors.
4. Disable V_{GSA} and V_{GSB} .

13 Component layout and parts list

13.1 Component layout



aaa-059935

Figure 3. A5G26H606W19N reference circuit component layout

13.2 Component designations and values

Table 14. A5G26H606W19N reference circuit component designations and values

Part	Description	Part Number	Manufacturer
C1, C2	18 pF chip capacitor	600F180JT250XT	ATC
C3	1.2 pF chip capacitor	600F1R2BT250XT	ATC
C4	0.3 pF chip capacitor	600F0R3BT250XT	ATC
C5	0.6 pF chip capacitor	600F0R6BT250XT	ATC
C6, C7, C12, C13, C14, C16, C18, C27, C28, C29, C31, C32, C33	10 μ F chip capacitor	GRM32EC72A106KE05L	Murata
C8	12 pF chip capacitor	600F120JT250XT	ATC
C9, C11, C26, C30	18 pF chip capacitor	800B180JT500XT	ATC
C10, C25	1 pF chip capacitor	600F1R0BT250XT	ATC
C17, C19, C36	5.6 pF chip capacitor	600F5R6BT250XT	ATC
C20	1.8 pF chip capacitor	600F1R8BT250XT	ATC
C21	2.2 pF chip capacitor	600F2R2BT250XT	ATC
C22	2.4 pF chip capacitor	600F2R4BT250XT	ATC
C23, C24	1.6 pF chip capacitor	600F1R6BT250XT	ATC
C34, C35	220 μ F, 100 V electrolytic capacitor	MCGPR100V227M16X26	Multicomp
Q1	RF power GaN amplifier	A5G26H606W19N	NXP
R1	50 Ω , 8 W termination chip resistor	C8A50Z4A	Anaren/TTM
R2	2.2 Ω , 1/8 W chip resistor	CRCW08052R20JNEA	Vishay
R3	0 Ω , 1/8 W chip resistor	CRCW08050000Z0EA	Vishay
R4	5.1 Ω , 1/8 W chip resistor	CRCW08055R10JNEA	Vishay
Z1	2300–2900 MHz, 90°, 3 dB PCB hybrid coupler	X3C26P1-03S	Anaren/TTM
PCB	Rogers RO4350B, 0.020", ϵ_r = 3.48	D192751	MTL

Note: Component number C15 is intentionally omitted.

14 Package information

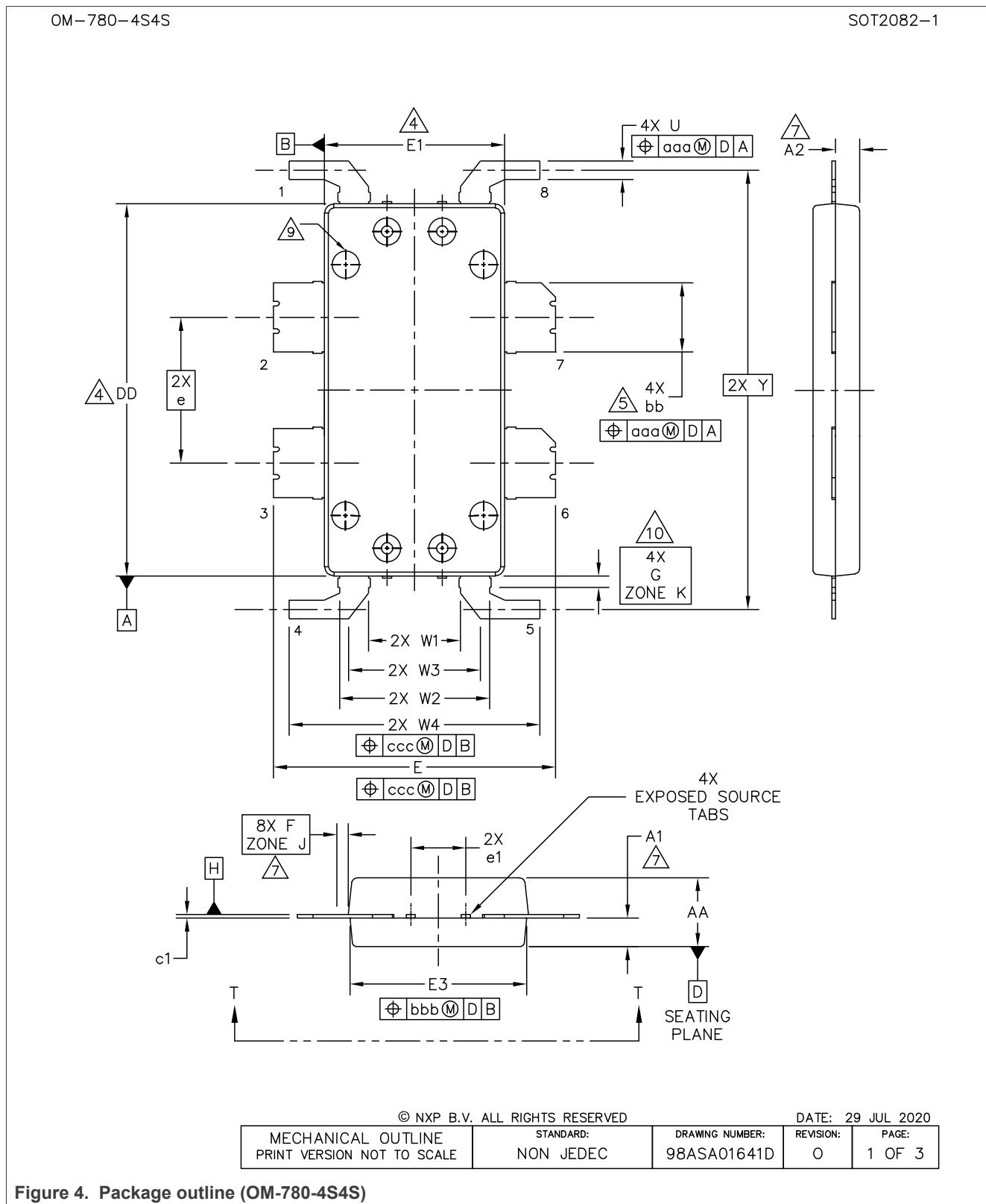
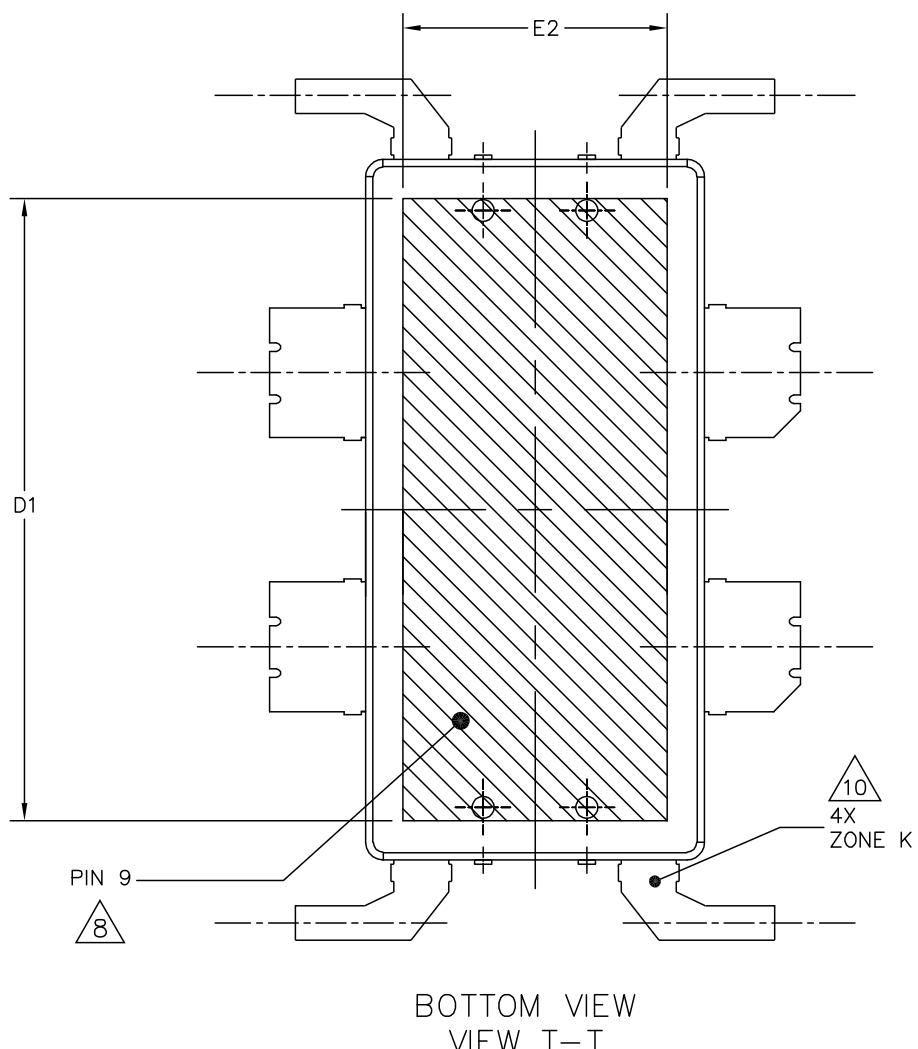


Figure 4. Package outline (OM-780-4S4S)

OM-780-4S4S

SOT2082-1



© NXP B.V. ALL RIGHTS RESERVED MECHANICAL OUTLINE PRINT VERSION NOT TO SCALE		STANDARD: NON JEDEC	DRAWING NUMBER: 98ASA01641D	DATE: 29 JUL 2020 REVISION: 0	PAGE: 2
--	--	------------------------	--------------------------------	----------------------------------	---------

Figure 5. Package outline (OM-780-4S4S) — bottom view

OM-780-4S4S

SOT2082-1

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE H IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS DD AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 INCH (0.15 MM) PER SIDE. DIMENSIONS DD AND E1 DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE H.
5. DIMENSION bb DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 INCH (0.13 MM) TOTAL IN EXCESS OF THE bb DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.
7. DIMENSIONS A1 AND A2 APPLIES WITHIN ZONE J ONLY. A1 APPLIES TO PINS 2, 3, 6 AND 7. A2 APPLIES TO PINS 1, 4, 5 AND 8.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. THE DIMENSIONS D1 AND E2 REPRESENT THE VALUES BETWEEN THE TWO OPPOSITE POINTS ALONG THE EDGES OF EXPOSED AREA OF HEAT SLUG.
9. DIMPLED HOLE REPRESENTS INPUT SIDE.
10. ZONE K REPRESENTS NON-SOLDERABLE REGION WHERE MOLD FLASH AND RESIN BLEED ARE PERMITTED ON BOTH SIDES OF THE LEADS.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.148	.152	3.76	3.86	W2	.321	.331	8.15	8.41
A1	.059	.065	1.50	1.65	W3	.281	.291	7.14	7.39
A2	.056	.068	1.42	1.73	W4	.538	.554	13.67	14.07
DD	.808	.812	20.52	20.62	U	.037	.043	0.94	1.09
D1	.720	----	18.29	----	Y	.956 BSC		24.28 BSC	
E	.610	.618	15.49	15.70	bb	.147	.153	3.73	3.89
E1	.390	.394	9.91	10.01	c1	.007	.011	0.18	0.28
E2	.306	----	7.77	----	e	.317 BSC		8.05 BSC	
E3	.383	.387	9.73	9.83	e1	.116	.124	2.95	3.15
F	.025 BSC		0.64 BSC		aaa	.004		0.10	
G	.030 BSC		0.76 BSC		bbb	.006		0.15	
W1	.195	.205	4.95	5.21	ccc	.010		0.25	

© NXP B.V. ALL RIGHTS RESERVED		DATE: 29 JUL 2020		
MECHANICAL OUTLINE PRINT VERSION NOT TO SCALE	STANDARD: NON JEDEC	DRAWING NUMBER: 98ASA01641D	REVISION: 0	PAGE: 3

Figure 6. Package outline (OM-780-4S4S) — notes, dimensions

15 Product documentation, software and tools

Refer to the following resources to aid your design process.

Application notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Software

- .s2p file

Development tools

- Printed circuit boards

16 Revision history

The following table summarizes revisions to this document.

Table 15. Revision history

Document ID	Release date	Description
A5G26H606W19N v.3.0	13 February 2026	<ul style="list-style-type: none">• Changed reference of "Transistor" to "Amplifier"
A5G26H606W19N v.2	3 Oct. 2025	<ul style="list-style-type: none">• Table 11: updated P_{sat} minimum from 55.5 dBm to 55.8 dBm to match final test limit, p. 4
A5G26H606W19N v.1	9 April 2025	<ul style="list-style-type: none">• Initial release of product data sheet

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <https://www.nxp.com>.

Definitions

Draft — A draft status on a document indicates that the content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included in a draft version of a document and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the Terms and conditions of commercial sale of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <https://www.nxp.com/profile/terms>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Suitability for use in non-automotive qualified products — Unless this document expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

HTML publications — An HTML version, if available, of this document is provided as a courtesy. Definitive information is contained in the applicable document in PDF format. If there is a discrepancy between the HTML document and the PDF document, the PDF document has priority.

Translations — A non-English (translated) version of a document, including the legal information in that document, is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

Security — Customer understands that all NXP products may be subject to unidentified vulnerabilities or may support established security standards or specifications with known limitations. Customer is responsible for the design and operation of its applications and products throughout their lifecycles to reduce the effect of these vulnerabilities on customer's applications and products. Customer's responsibility also extends to other open and/or proprietary technologies supported by NXP products for use in customer's applications. NXP accepts no liability for any vulnerability. Customer should regularly check security updates from NXP and follow up appropriately. Customer shall select products with security features that best meet rules, regulations, and standards of the intended application and make the ultimate design decisions regarding its products and is solely responsible for compliance with all legal, regulatory, and security related requirements concerning its products, regardless of any information or support that may be provided by NXP.

NXP has a Product Security Incident Response Team (PSIRT) (reachable at PSIRT@nxp.com) that manages the investigation, reporting, and solution release to security vulnerabilities of NXP products.

NXP B.V. — NXP B.V. is not an operating company and it does not distribute or sell products.

Trademarks

Notice: All referenced brands, product names, service names, and trademarks are the property of their respective owners.

NXP — wordmark and logo are trademarks of NXP B.V.

Airfast — is a trademark of NXP B.V.

Tables

Tab. 1.	2600 MHz — Typical Doherty single-carrier W-CDMA reference circuit performance	1
Tab. 2.	Ordering information	2
Tab. 3.	Product marking trace code	2
Tab. 4.	Limiting values	3
Tab. 5.	Recommended operating conditions	3
Tab. 6.	Thermal characteristics	3
Tab. 7.	ESD protection characteristics	3
Tab. 8.	Moisture sensitivity level	3
Tab. 9.	DC characteristics — off characteristics	4
Tab. 10.	DC characteristics — on characteristics	4
Tab. 11.	Functional tests	4
Tab. 12.	Wideband ruggedness	5
Tab. 13.	Typical performance	5
Tab. 14.	A5G26H606W19N reference circuit component designations and values	7
Tab. 15.	Revision history	11

Figures

Fig. 1.	Pin configuration	2
Fig. 2.	Product marking	2
Fig. 3.	A5G26H606W19N reference circuit component layout	6
Fig. 4.	Package outline (OM-780-4S4S)	8
Fig. 5.	Package outline (OM-780-4S4S) — bottom view	9
Fig. 6.	Package outline (OM-780-4S4S) — notes, dimensions	10

Contents

1	General description	1
2	Features and benefits	1
3	Typical performance	1
4	Pinning information	2
5	Ordering information	2
6	Product marking	2
7	Limiting values	3
8	Recommended operating conditions	3
9	Thermal characteristics	3
10	ESD protection characteristics	3
11	Moisture sensitivity level	3
12	Electrical characteristics	4
12.1	DC characteristics — off characteristics	4
12.2	DC characteristics — on characteristics	4
12.3	Functional tests	4
12.4	Wideband ruggedness	5
12.5	Typical performance	5
13	Component layout and parts list	6
13.1	Component layout	6
13.2	Component designations and values	7
14	Package information	8
15	Product documentation, software and tools	11
16	Revision history	11
	Legal information	12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.